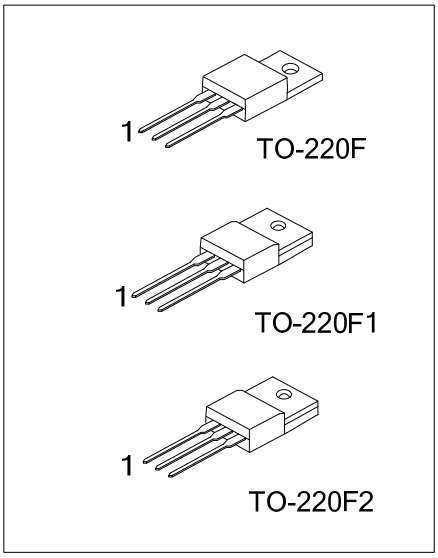
10N50K-MT

Power MOSFET

10A, 500V N-CHANNEL POWER MOSFET



■ DESCRIPTION

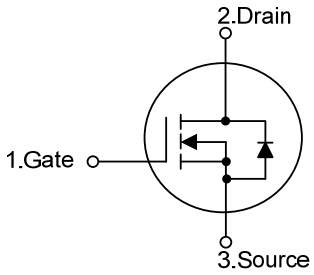
The UTC **10N50K-MT** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **10N50K-MT** is generally applied in high efficiency switch mode power supplies, active power factor correction and electronic lamp ballasts based on half bridge topology.

■ FEATURES

* $R_{DS(ON)} \leq 0.68\Omega$ @ V_{GS}=10V, I_D=5.0A
* High Switching Speed
* 100% Avalanche Tested

■ SYMBOL



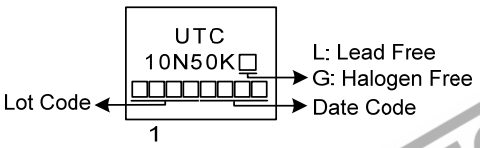
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
10N50KL-TF1-T	10N50KG-TF1-T	TO-220F1	G	D	S	Tube
10N50KL-TF2-T	10N50KG-TF2-T	TO-220F2	G	D	S	Tube
10N50KL-TF3-T	10N50KG-TF3-T	TO-220F	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

10N50KG-TF1-T (1)Packing Type (2)Package Type (3)Green Package	(1) T: Tube (2) TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F (3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	500	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous (T_C=25°C)	I_D	10 (Note 2)	A
	Pulsed (Note 3)	I_{DM}	20 (Note 2)	A
Avalanche Current (Note 3)		I_{AR}	10	A
Avalanche Energy	Single Pulsed (Note 4)	E_{AS}	245	mJ
Peak Diode Recovery dv/dt (Note 5)		dv/dt	4.5	V/ns
Power Dissipation		P_D	48	W
Derate above 25°C			0.38	W/°C
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Drain current limited by maximum junction temperature.
3. Repetitive Rating: Pulse width limited by maximum junction temperature.
4. L = 10mH, I_{AS} = 7A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
5. I_{SD} ≤ 10A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

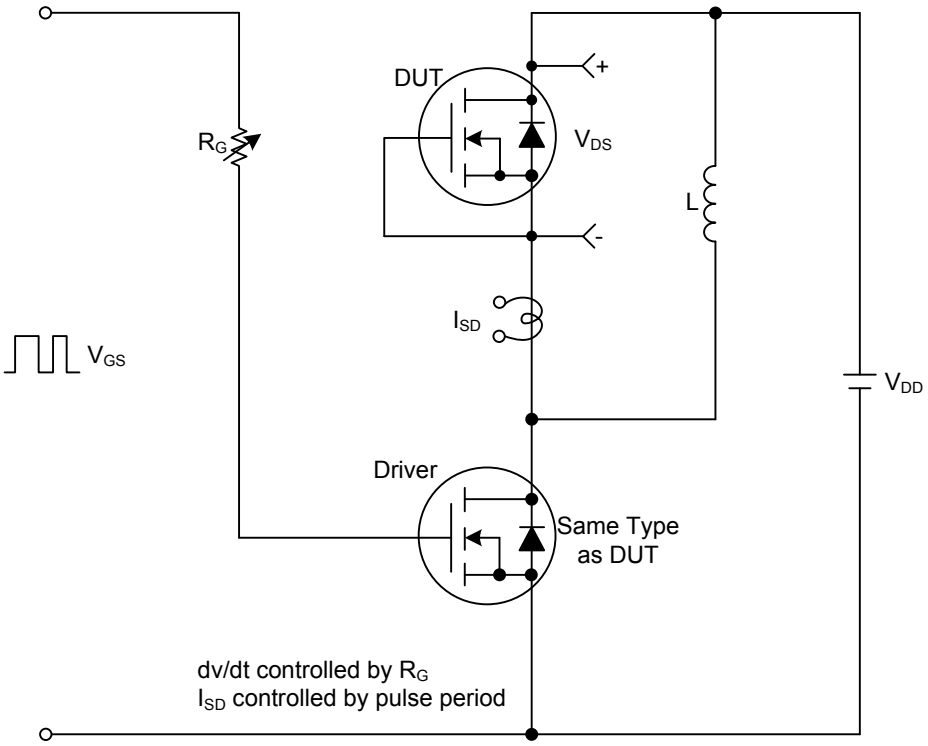
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	°C/W
Junction to Case	θ_{JC}	2.58	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

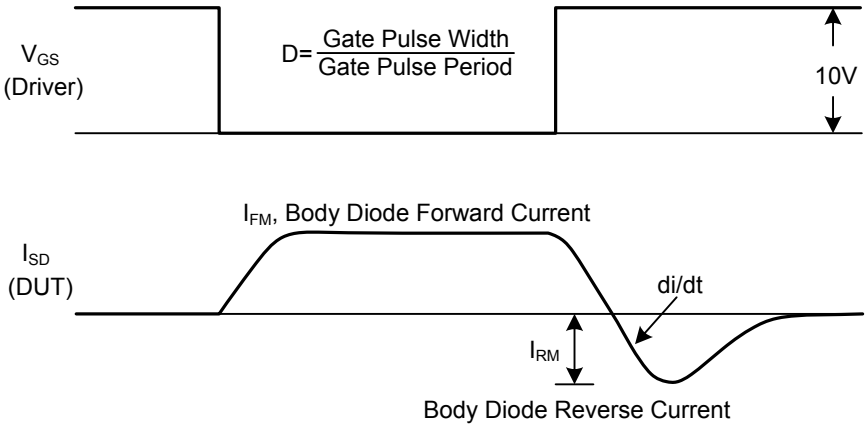
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	500			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=500V, V_{GS}=0V			10	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=5.0A			0.68	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		1322		pF
Output Capacitance		C_{OSS}			140		pF
Reverse Transfer Capacitance		C_{RSS}			7.5		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{DS}=100V, V_{GS}=10V, I_D=10A, I_G=1mA		35		nC
Gate to Source Charge		Q_{GS}			7.6		nC
Gate to Drain Charge		Q_{GD}			4		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=100V, V_{GS}=10V, I_D=10A, R_G=25Ω		16.8		ns
Rise Time		t_R			82		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			58.2		ns
Fall-Time		t_F			19.6		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				10	A
Maximum Body-Diode Pulsed Current		I_{SM}				20	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=10A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time		t_{rr}	I_S=10A, V_{GS}=0V, dI_F/dt=100A/μs		352		nS
Body Diode Reverse Recovery Charge		Q_{rr}			4.4		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

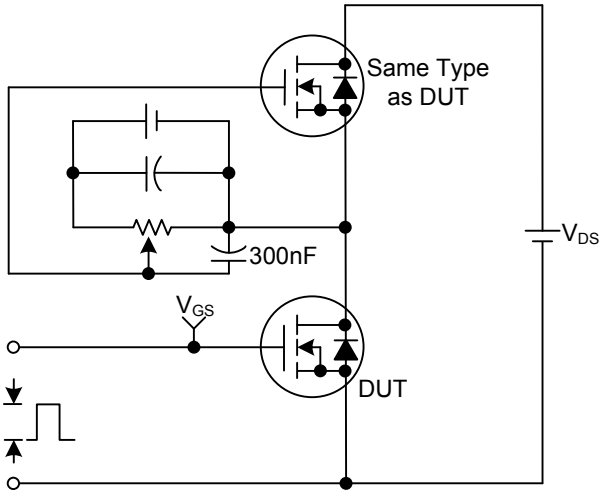


Peak Diode Recovery dv/dt Test Circuit & Waveforms

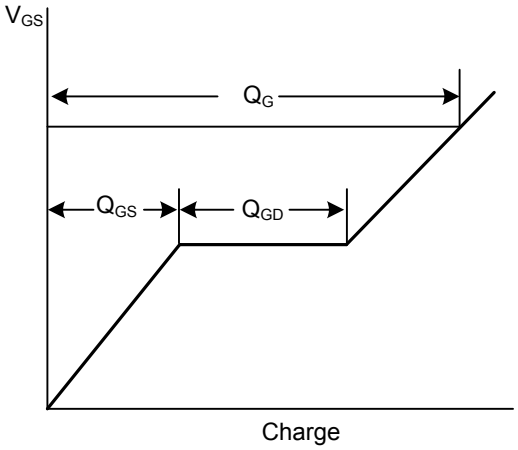


Peak Diode Recovery dv/dt Waveforms

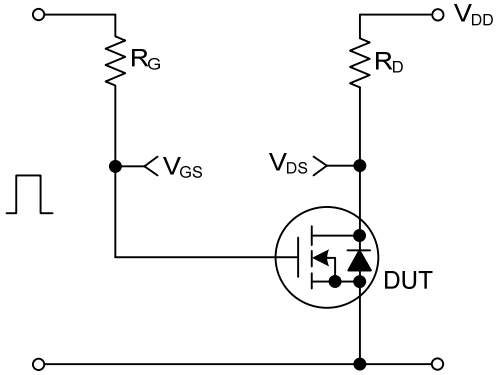
■ TEST CIRCUITS AND WAVEFORMS



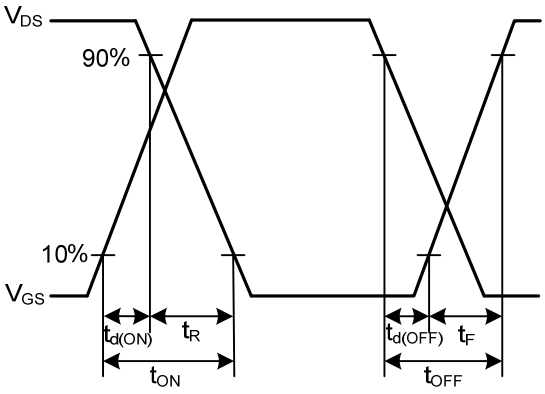
Gate Charge Test Circuit



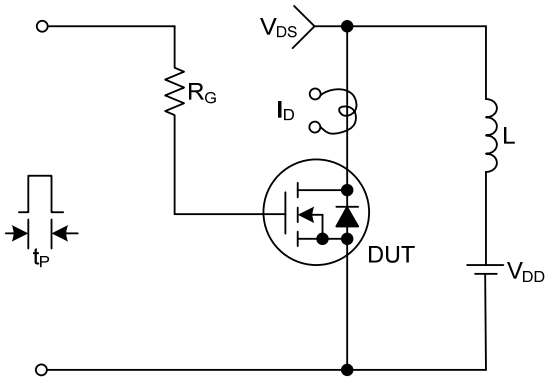
Gate Charge Waveforms



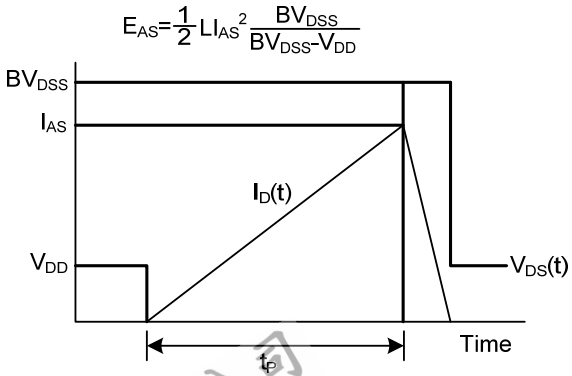
Resistive Switching Test Circuit



Resistive Switching Waveforms



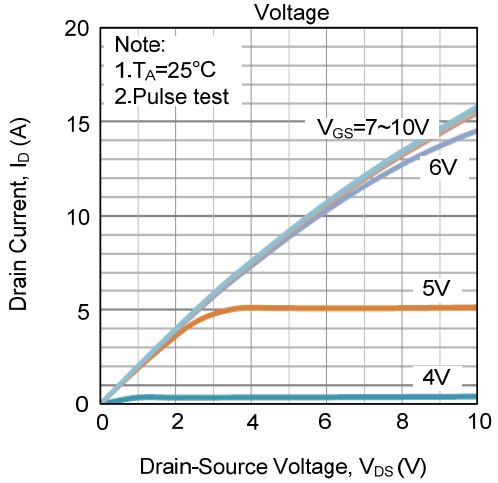
Unclamped Inductive Switching Test Circuit



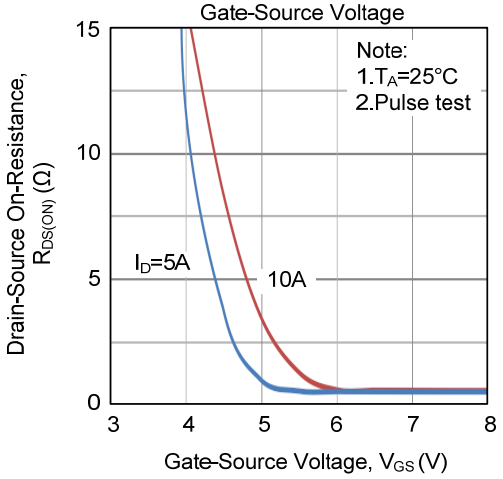
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

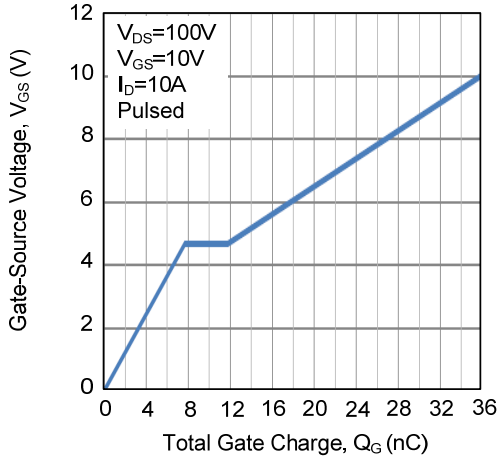
Drain Current vs. Drain-Source Voltage



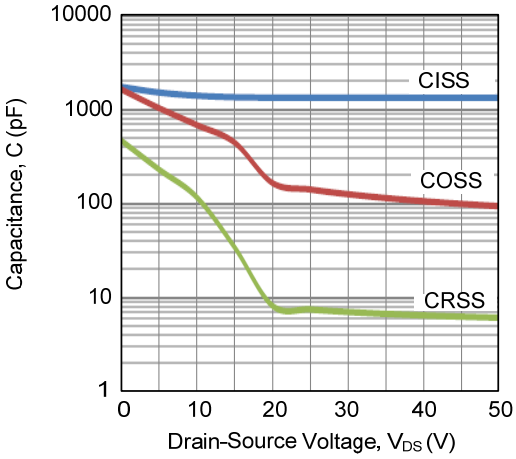
Drain-Source On-Resistance vs. Gate-Source Voltage



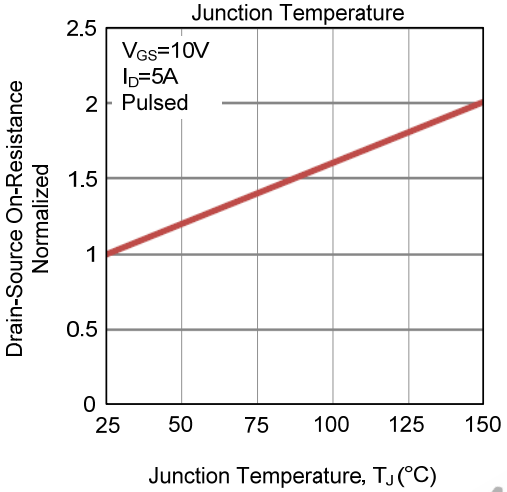
Gate Charge Characteristics



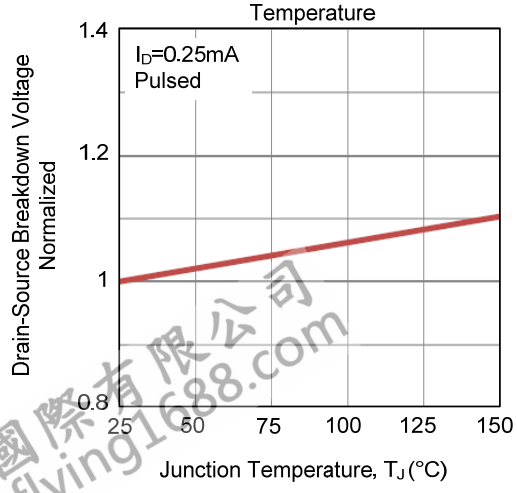
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

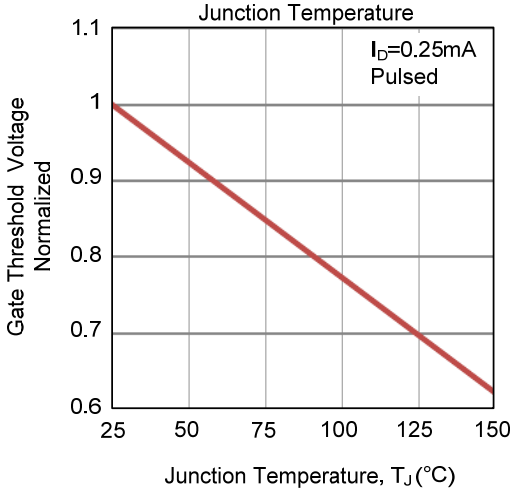


Breakdown Voltage vs. Junction Temperature

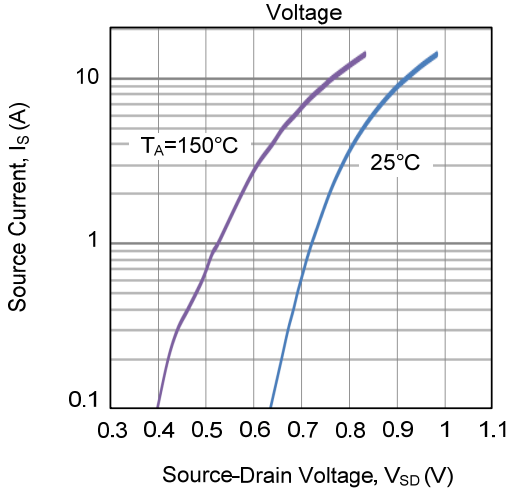


■ TYPICAL CHARACTERISTICS (Cont.)

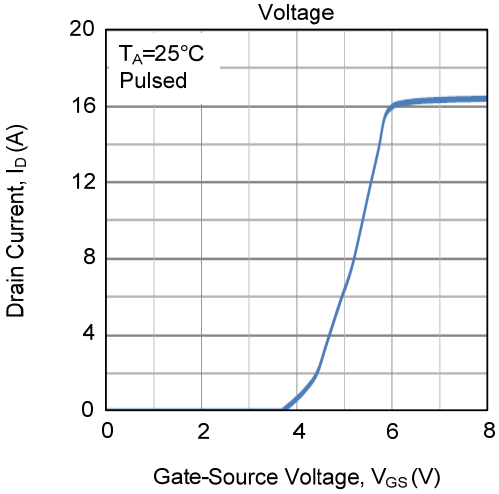
Gate Threshold Voltage vs. Junction Temperature



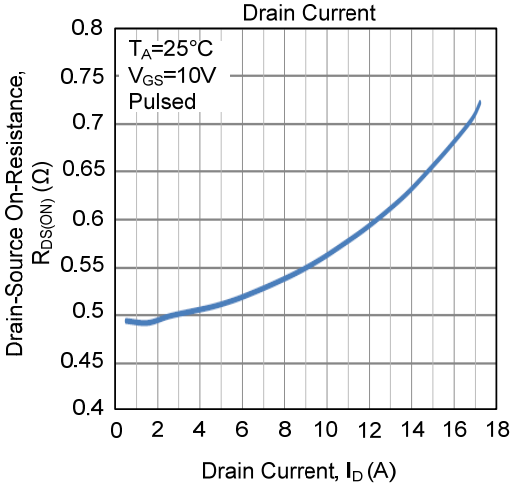
Source Current vs. Source-Drain Voltage



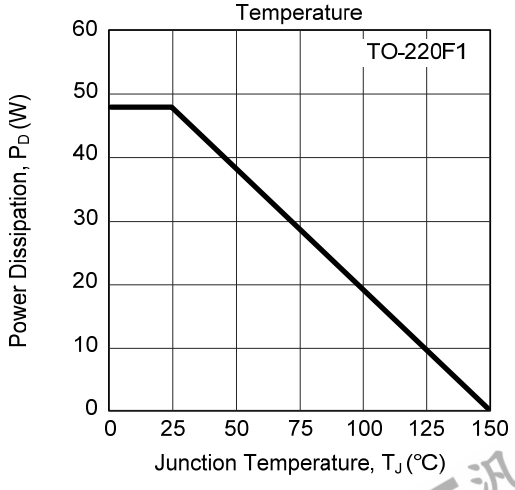
Drain Current vs. Gate-Source Voltage



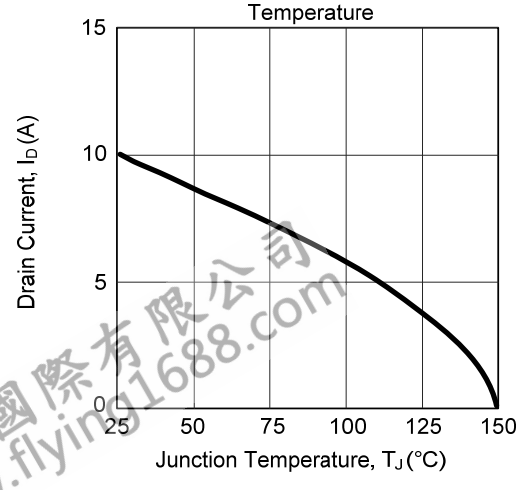
Drain-Source On-Resistance vs. Drain Current



Power Dissipation vs. Junction Temperature



Drain Current vs. Junction Temperature



■ TYPICAL CHARACTERISTICS (Cont.)